

Kevin K. Yee (Samsung), Fakhruddin Ali Bohra (Arm), Edson Gomersall (Cadence) Arm TechCon 2019 San Jose Oct. 9, 2019







SAMSUNG FOUNDRY High-Performance 5LPE Implementation Next-Generation Arm "Hercules" CPU

Kevin K. Yee Marketing Director, IP & Ecosystem Samsung Foundry







Cadence, Arm, Samsung Foundry Partnership



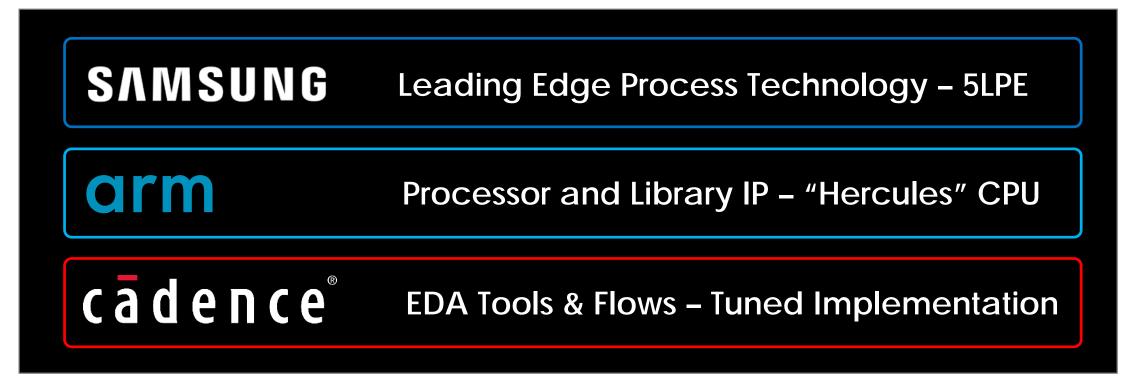






Cadence, Arm, Samsung Foundry Collaboration

Enabling the Next Level of Innovation



Delivering the Most Optimized High-Performance Solution!

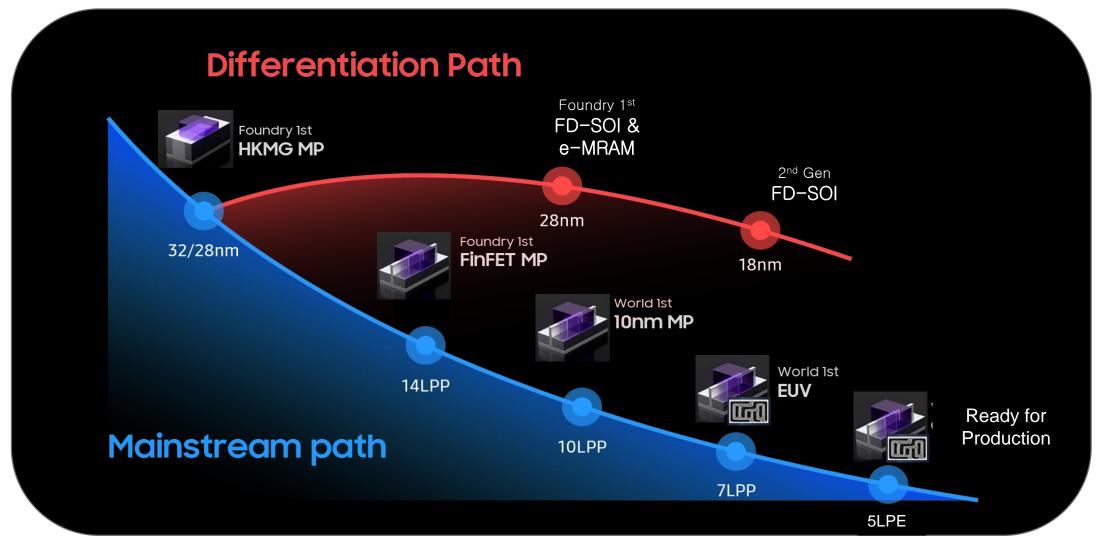






Samsung Foundry Technology Leadership

Leading the industry with many 1st



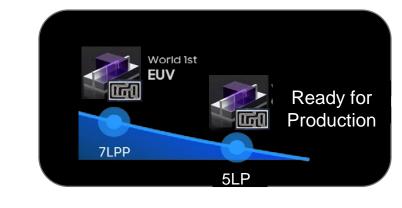


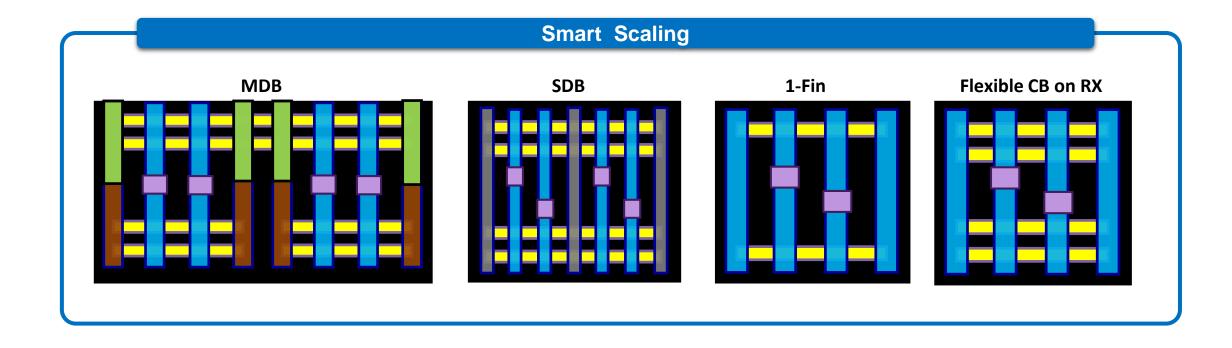


Why 5LPE?

Full EUV technology – ready for production

- 2nd gen. EUV technology
- # 7LPP compatibility: IP re-use, yield leverage, easy migration
- Enhanced features to 7LPP: MDB, SDB, single fin cell, CB on RX edge









5LPE Process Overview

Easy migration from 7LPP

IP re-usability with boosted transistor performance

- GR compatibility, same SRAM, same TR structure
- 1.11x perf boosted by Low-k spacer, DC enhancement, etc.

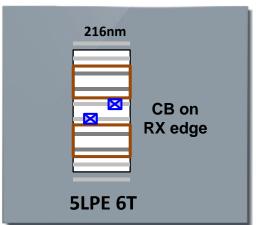
Smart scaling with 6T SC offering

0.70x block-level area due to 6T with SDB and CB on RX edge

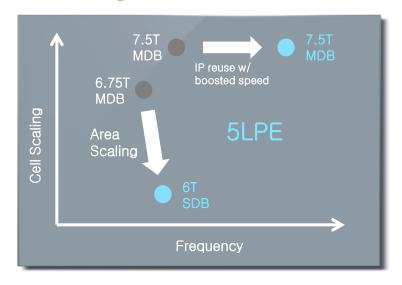
Superior power efficiency by 6T SDB with 1-Fin

0.80x block-level power

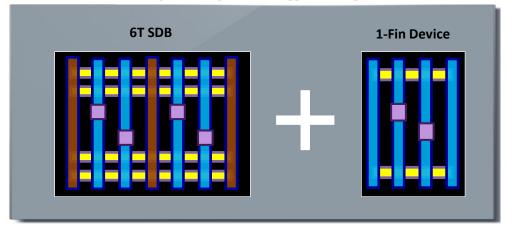




Migration Enhancement



Superior power efficiency





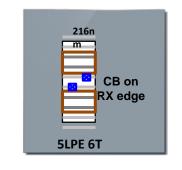


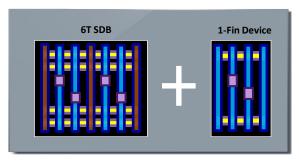


5LPE Technology Enhancements

Enabling 36M2, SDB, 1FIN, CB on RX-edge & 6T







	7LPP	5LPE	Note
FP	27FP		Compatible
СРР	54CPP/60CPP		Compatible
SRAM bitcell	P026/P032		Compatible
Vop, Vth, Lgate	0.75V, RVT/LVT/SLVT, 8nm/10nm		Compatible
M1/M3/M4	40nm/36nm/44nm		Compatible
M2	48nm + 36nm		Enhance
Diffusion Break	MDB	+ SDB	Enhance
Min NFIN	2FIN + 1FIN		Enhance
СВ	CB on STI	+ CB on RX-edge	Enhance
Standard Cell	7.5T	+ 6T	Enhance





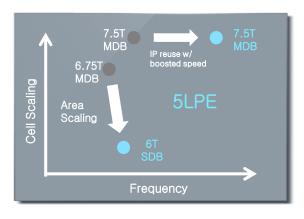
5LPE Key Feature Comparison

7.5T for performance, 6T for area & power

T.5T: Performance driven with 60CPP and MDB

6T: Area & power driven with CB of RX edge, SDB and 36M2

Track		7.5T [HD]	6T [UHD]	
Cell Height [nm]		270	216	
Tech Definition	FP [nm]	27	27	
	CPP [nm]	60	54	
	M1 [nm]	40Bi	40Uni	
	M2 [nm]	60	36	
	DB	MDB	SDB	
	СВ	CB on STI	CB on RX edge	
Design Feature	FIN#	3:3	2:2	
	Signal Track	6	5	







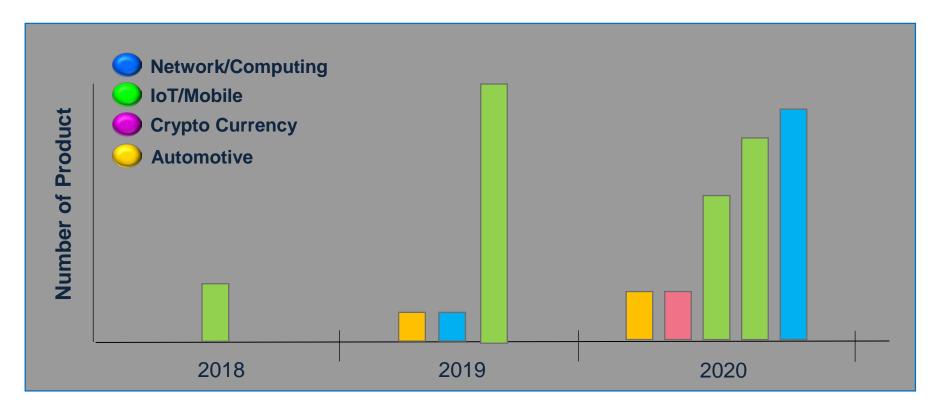
5LPE Broad Market Adoption

7.5T for performance, 6T for area & power

4018: 7nm production tapeout

3019: 5nm production tapeout

2020: Main node will be 5nm







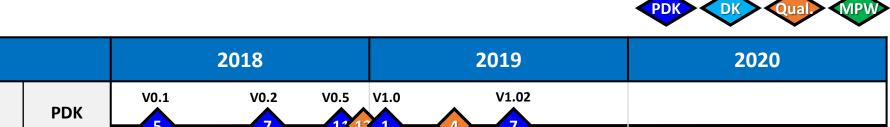
5LPE Availability

Key milestones

PDK v1.0: Released Jan'19

L1+168H: Completed Apr. '19

MPW MTO: Feb'19







Samsung Advanced Foundry Ecosystem



Join us!

9am – 7pm October 17, 2019 SAMSUNG@FIRST CAMPUS

REGISTER NOW!:

https://events.samsungatfirst.com/foundry-safe-forum-2019/





Fakhruddin Ali Bohra Senior Principal Design Engineer Arm

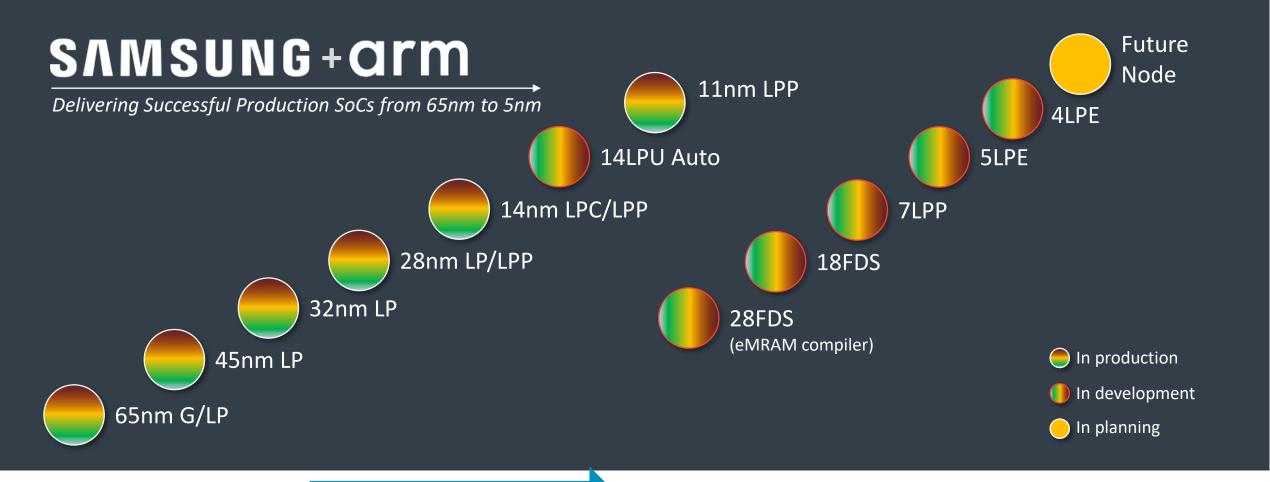






Arm Artisan Physical IP and Samsung Foundry Partnership

Over 3 billion chips shipped with Arm Artisan Physical IP



arm DESIGNSTART







Arm Artisan on Samsung Foundry 5LPE (EUV) Platform

Standard Cell



- Comprehensive cell set for broad application coverage
- 7.5 & 6 UHD Track Library
- Power management & ECO



Memory Compiler

- 8 memory compilers
- Low VDD assist features
- Multi periphery Vt options
- Extensive features set

Physical Design Group Products

arm Artisan



GPIO

- GPIO 1.8V
- GPIO 3.3V

Architect

- Logic libraries
- Memory compiler

POPTM IP

- Cortex-A76
- Cortex-A55
- Hercules
- All POP with DynamIQ™

Complete Physical IP Platform

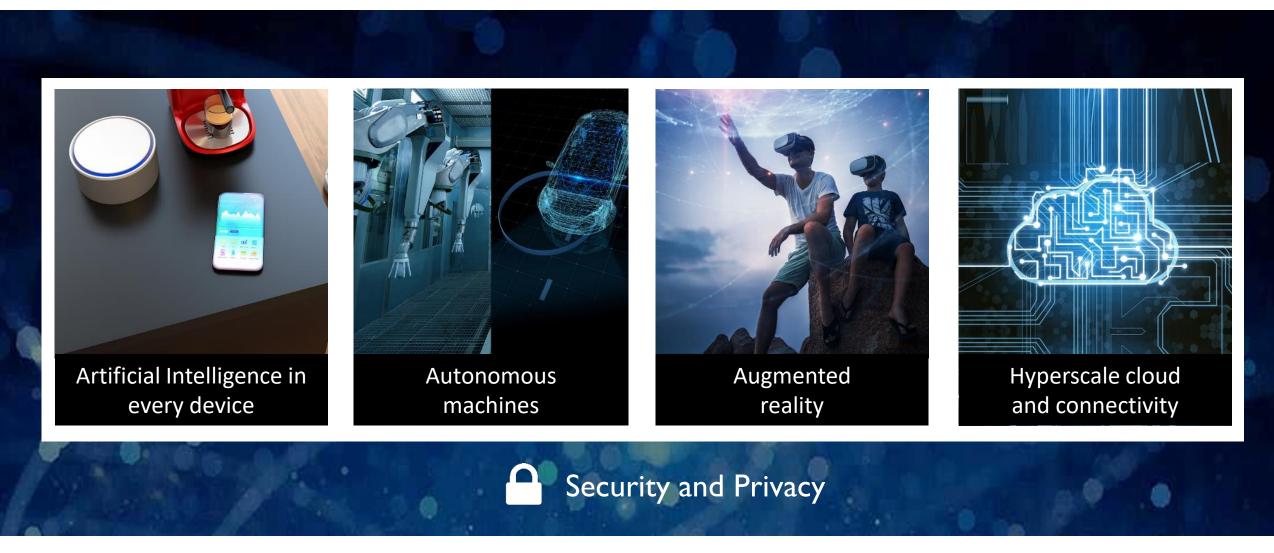
- Foundry sponsored foundation IP
 Support wide range of applications from mobile, consumer and automotive
- POP IP for "Hercules" CPU, Arm® Cortex®-A76 and Cortex-A55 based computing systems
- Design kits available







Technology Trends that Will Redefine All Industries





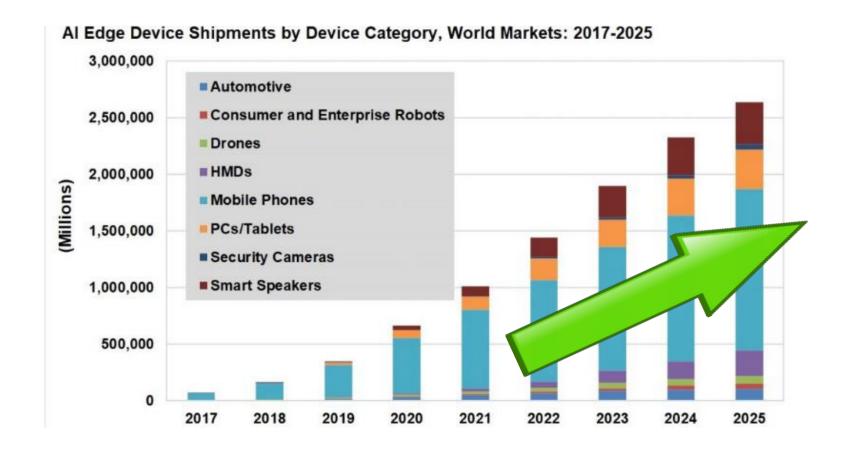




Al is Everywhere

Industry landscape: What trends will drive the industry

- Al cuts across applications spaces
- Projected
 continued growth
 across all
 applications



Source : Tractica (2018)

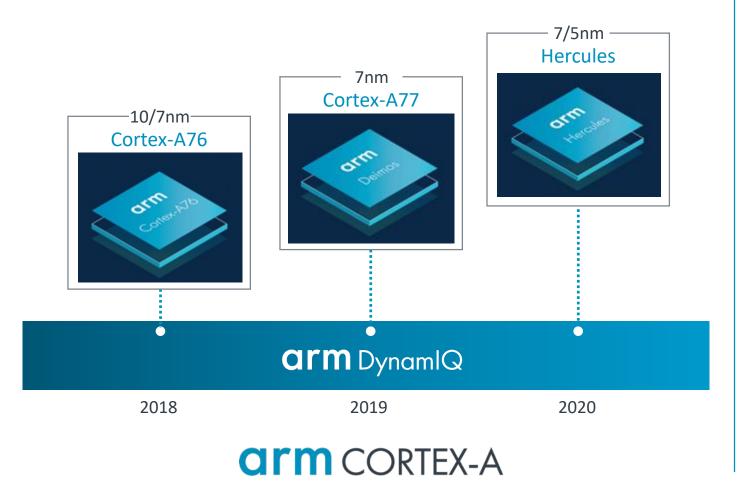






Breakthrough Performance for Always-On, Always-Connected

Continuing the trajectory of increased compute performance for AI, ML and premium mobile



Cortex-A76: High-performance implementation: 3+ GHz in 7nm

Cortex-A77: Up to 20% improved IPC performance

Hercules: Continuing performance and efficiency leadership

Supports the flexibility of Arm DynamIQ big.LITTLE™







Translating Arm RTL Benefits into Silicon

HOW TO

Translate
the year-over-year
performance
improvements of
>15% for compute
through 2020 in silicon

?

Optimize implementation for new cores and advanced process nodes

Ensure **fast turn- around time** such that increased productivity of new Arm cores

?

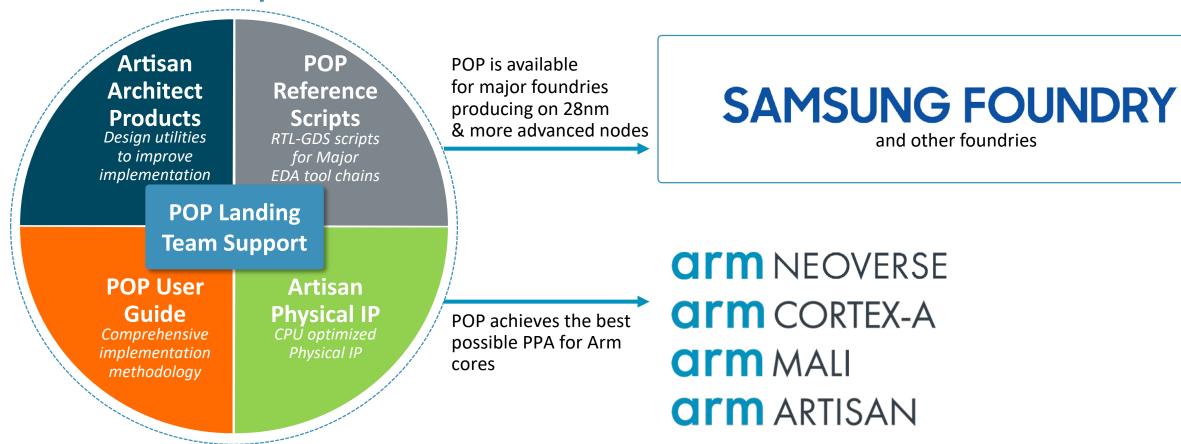






Arm POP IP is Optimized Arm Core Implementation

POP IP Components



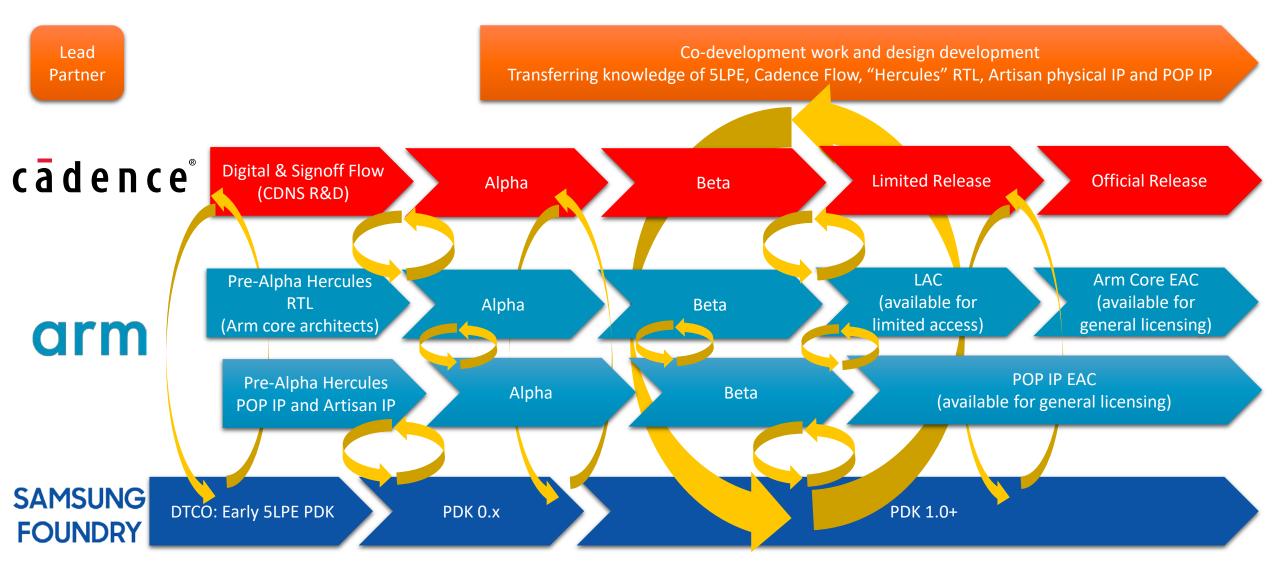
Comprehensive support and services







Design Technology Co-Optimization (DTCO) Benefits the Ecosystem







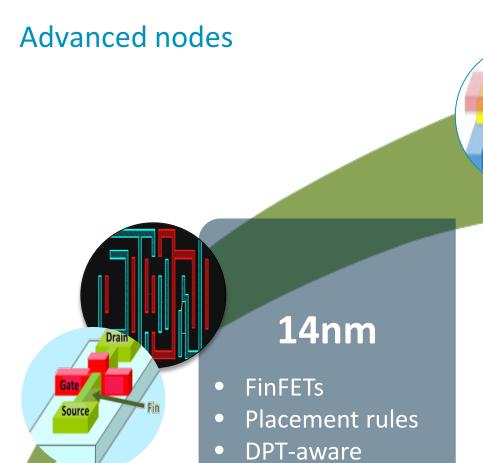


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Implementation Challenges

Challenges present for advanced nodes and cores

colorless routing



Latest Arm Cores

- Concurrent configuration of CPU with DynamIQ Shared Unit (DSU)
- Asynchronous configuration
- Long channels between
 DSU and CPU slaves
- Private L2 cache
- Architectural clock gating



5_{nm}

Via ladders

rules

Power grid

Addressing

variation

challenges

New placement





5LPE: Continued Enhancements for Artisan Logic IP

Performance

- New compressor cells
- New flip-flops: 30% performance gain per cell level

Power

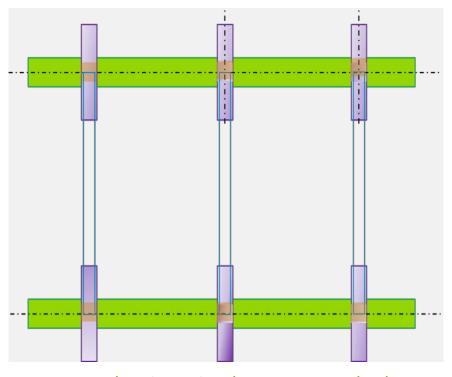
- New multi-bit functional cells
- Low power flip-flops

Density

- Key combinatorial cells: 5-10% area gains per cell level
- Flip-flops: 10+% area gains per cell level

Implementation

- Cells crafted to enable flexible cell placement while maintaining a tight and regular lower grid
- Utilities included to ease power grid generation
- Post-route opportunistic M2 stitching supported to improve EM/IR drop
- Large clock drivers for ideal H-Tree implementation
- Power gate design ensures no break in grid regularity



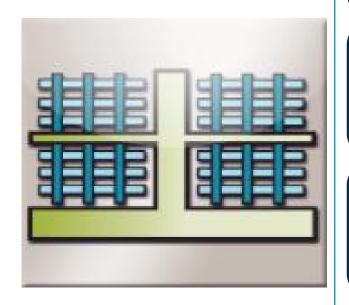
Dependencies exists between standard cell architecture & power grid;
Proper grid required for optimization







5LPE: Continued Enhancements for Artisan Memory IP



Performance

- Special optimization for key compilers
- Bitcell selection to match 5LPE target markets
- Multiple level shifting options for optimized DVFS at SOC level
- Careful wireplaning to mitigate RC

Power

- Compile-time options for core and periphery separation, control, retention and power down
- Multiple architecture and micro architecture changes

Density

- Extensive MUX, bank and slice options
- Innovative assist scheme
- Newer topological options

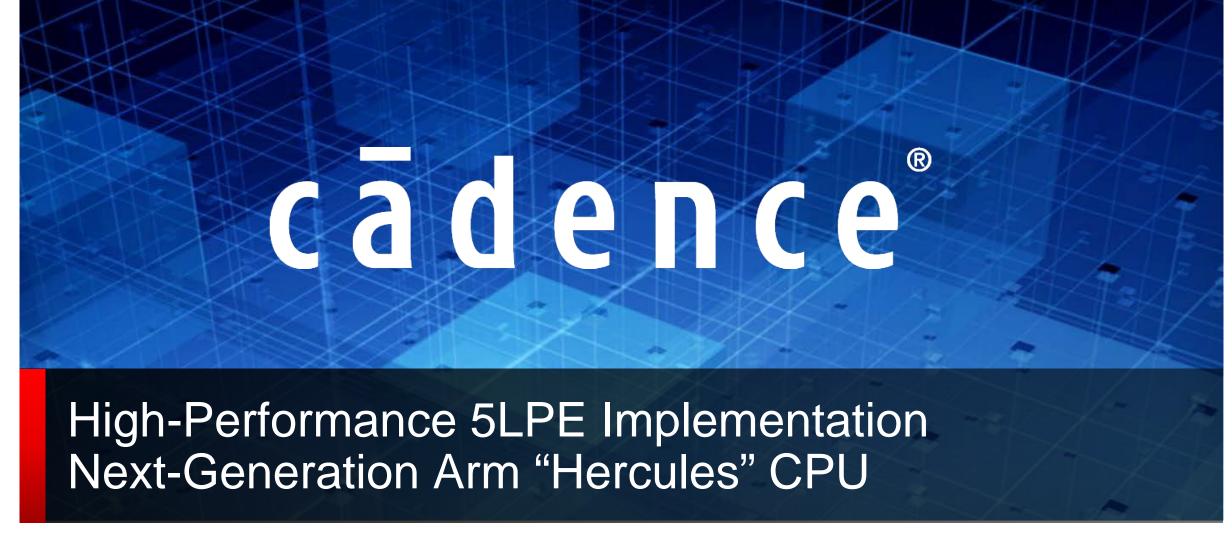
Implementation

• Instance layout minimizes placement and abutment restrictions









Edson Gomersall Product Engineering Architect Cadence

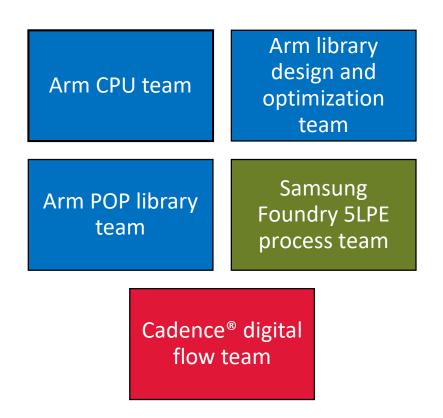


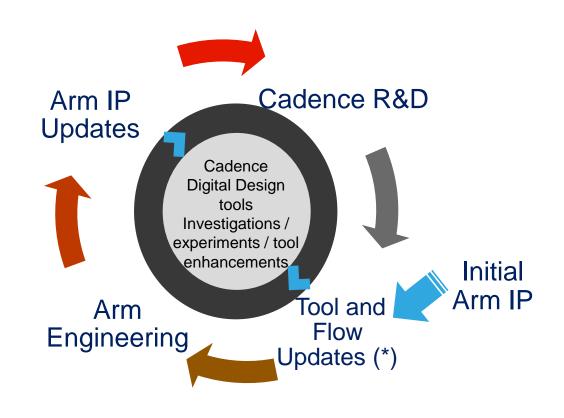




Cadence, Arm, and Samsung Foundry Collaboration

Worldwide engineering relationship





• Collaboration enables high-performance flow to be delivered

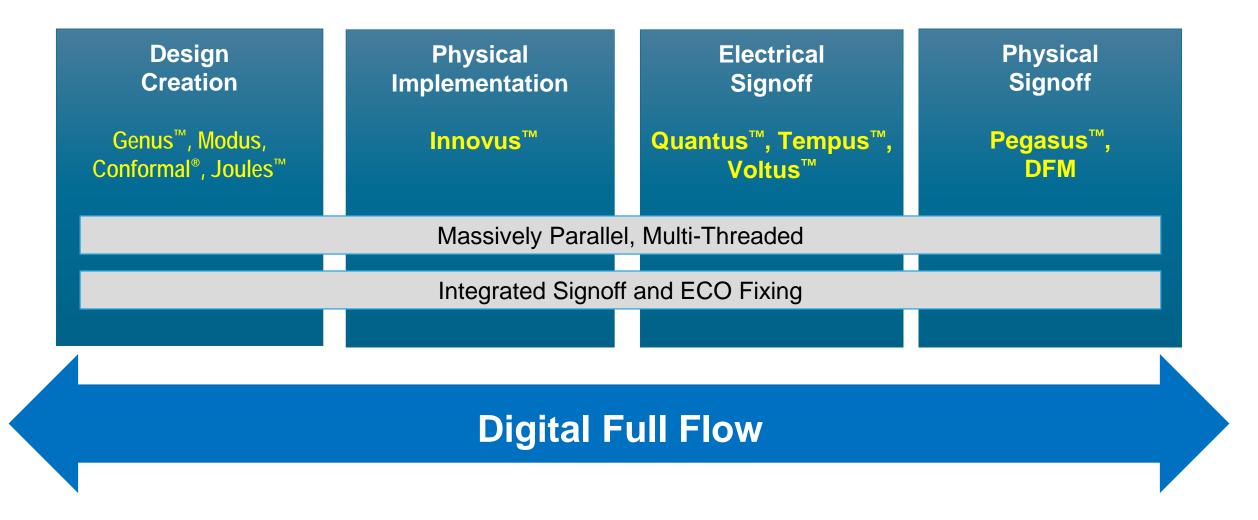
(*) Early collaboration ensures tool support in place







Arm CPU 5LPE Digital and Signoff Flow









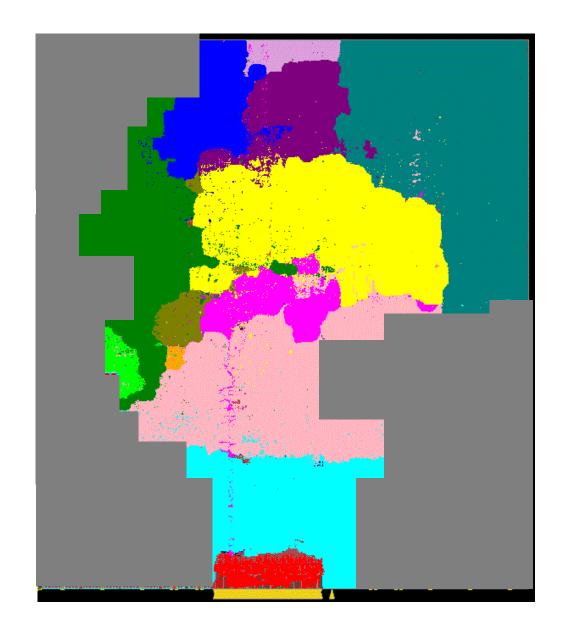
Arm CPU 5LPE Design Configuration

Process

- Samsung Foundry 5LPE
- 13 Layer Metal stack

CPU Core Overview

- Arm CPU 5LPE POP 7.5T standard cells
- Arm CPU 5LPE POP FCI memories
- Arm CPU floorplan
- Multiple voltage islands



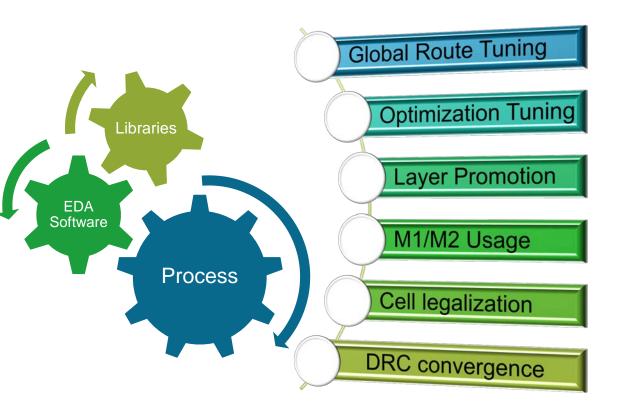






Cadence and Samsung Foundry 5LPE Co-Optimization

5LPE Process and Tool Co-Optimization



 One simple option to enable all 5LPE process support

setDesignMode -process 5 -node S5

Metric	After eGR tuning	
Frequency	14% improvement	
Utilization	7% improvement	

Early Global Route Tuning

	M4	D5	D6	D7	D10
Before tuning	80.5	77.9	84.2	51.5	43.2
After tuning	81.4	79.7	85.5	52.7	61.3

Layer Promotion Adherence

Out-of-Box Better Full Flow PPA

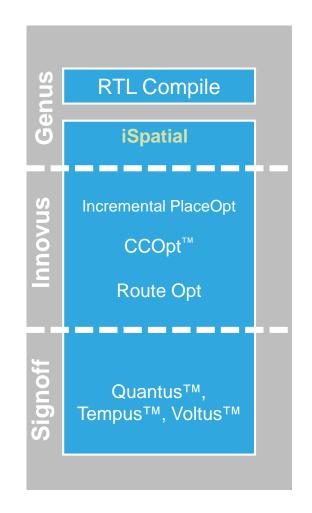






5LPE and CPU Characteristic Driven Features

5LPE-driven features	CPU-driven features	
Early global route tuning	Floorplan regions/guides	
Layer promotion	ICG placement optimization	
NDRs for specific layers	Custom cost groups	
Cell legalization	Strategic pre-skewing	
Statistical Via support	Clock tuning	







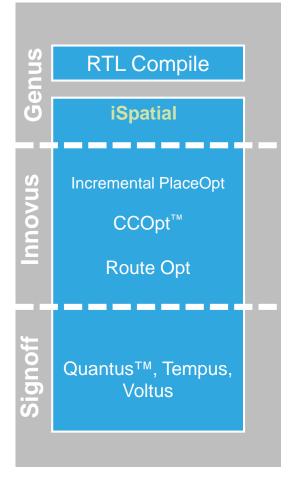


Cadence Digital Flow Benefits

- Combined Genus[™] and Innovus[™] solution with common optimization
 - iSpatial technology
 - 2x TAT improvement, 5% PPA benefit
- IR drop-aware flow
 - Integrated IR drop repair flow
- True signoff
 - Completely integrated with industry-leading Innovus Implementation System
 - Tempus™ and Voltus™ solutions combined is TRUE SIGNOFF
 - Via variation-aware timing signoff
- Stylus common UI
 - Usability and productivity enabler







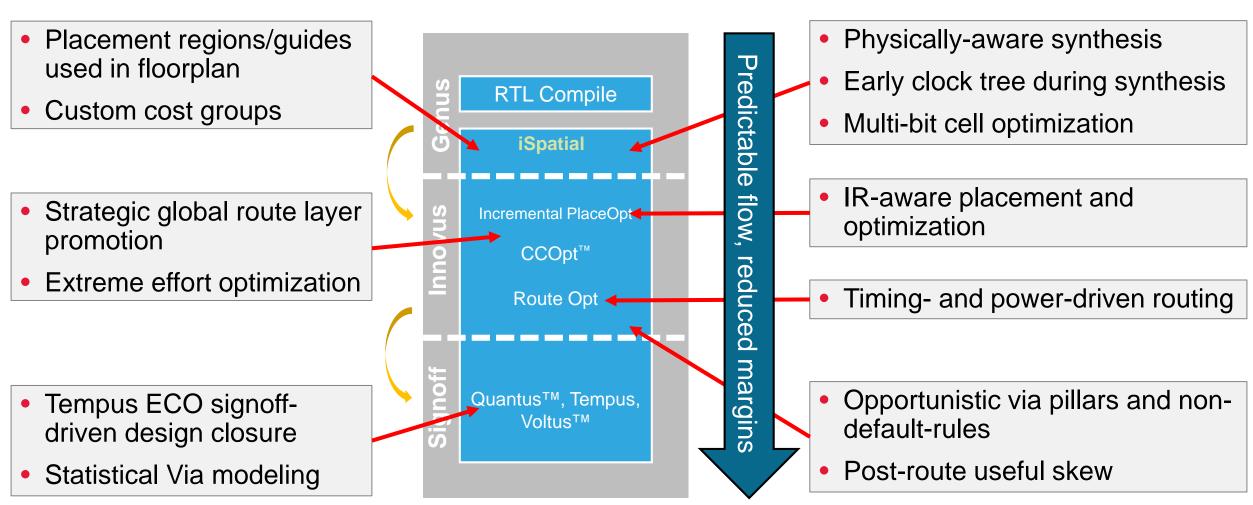






Arm CPU 5LPE iSpatial High-Performance Flow

Turn-around time and predictability benefits



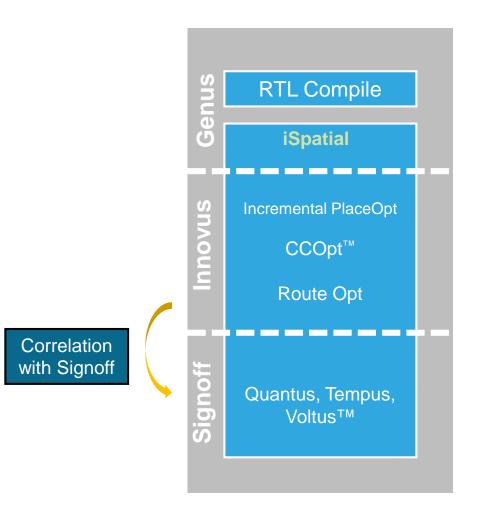
Mesh and Flex-H clock distribution supported which can influence design performance







5LPE Statistical Via Timing Analysis and Optimization



- Exclusive feature used in 5LPE signoff flow
- Global Via resistance variation modelled in extraction technology files
- Local Via resistance variation is modelled statistically by the foundry
 - Samsung Foundry provides mean shift and standard deviation of via cut sizes
 - Quantus[™] Extraction provides via resistance for each via
- Tempus[™] delay calculation engine uses both global and local resistance variation to ensure timing convergence during the flow
 - Part of the Samsung Foundry 5LPE signoff requirements
- Tempus ECO optimization accounts for all Via resistance effects







Concurrent Timing, Power, and IR Drop Optimization

Innovus, Tempus, Voltus single data model integration

Multi-Stage IR Correction RTL Compile **iSpatial** Incremental PlaceOpt CCOpt™ Route Opt Quantus™, Tempus™, Voltus™

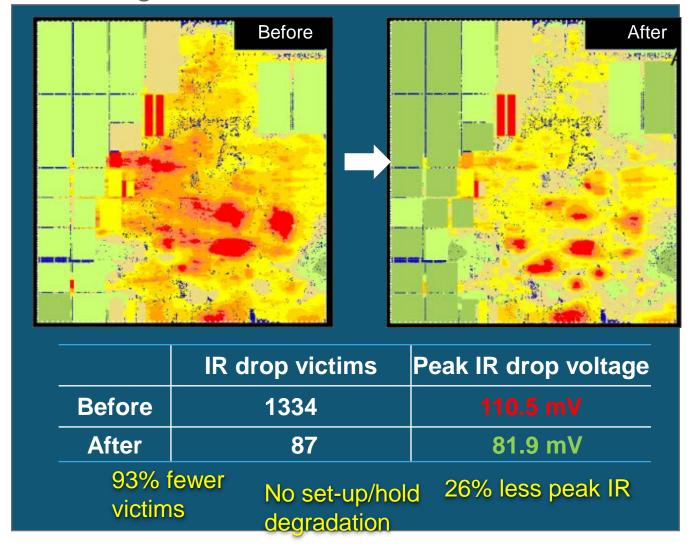
Early Rail Analysis

IR Drop-Aware Placement

Clock Useful Skew for Peak Power

Power Routing and Via Optimization

Timing And IR Drop-Aware ECO



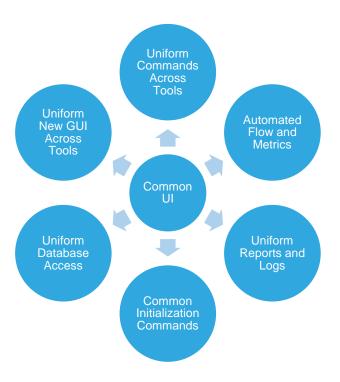






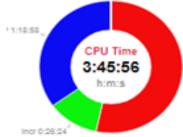
Full-Flow Unified Interface and Flow for Digital Implementation

Common User Interface



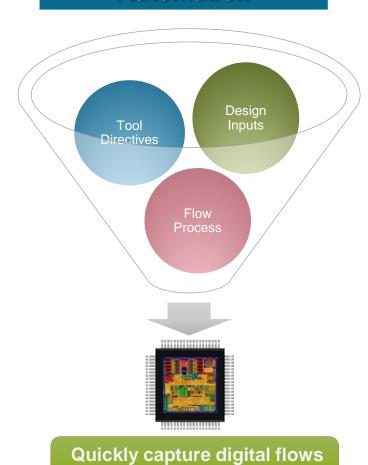
Unified Metrics





Consistent PPA reporting across the whole digital flow

Flow Capture and Automation







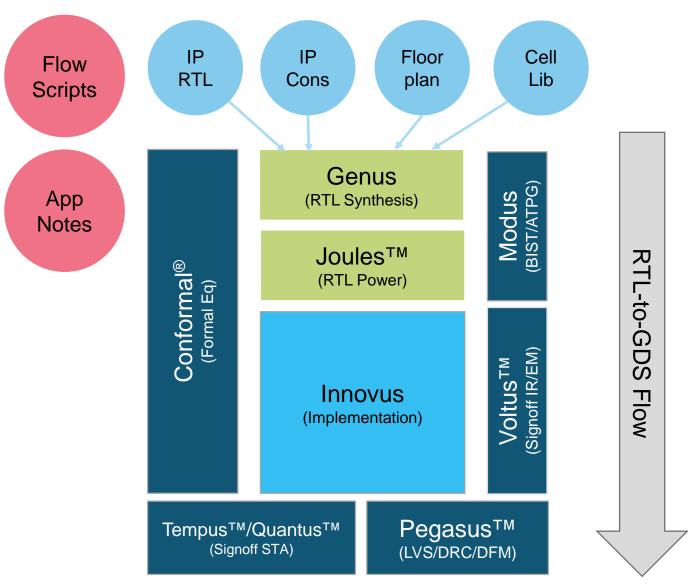
and deploy to users





Improved ease of use and designer productivity

Arm CPU 5LPE High-Performance Rapid Adoption Kit



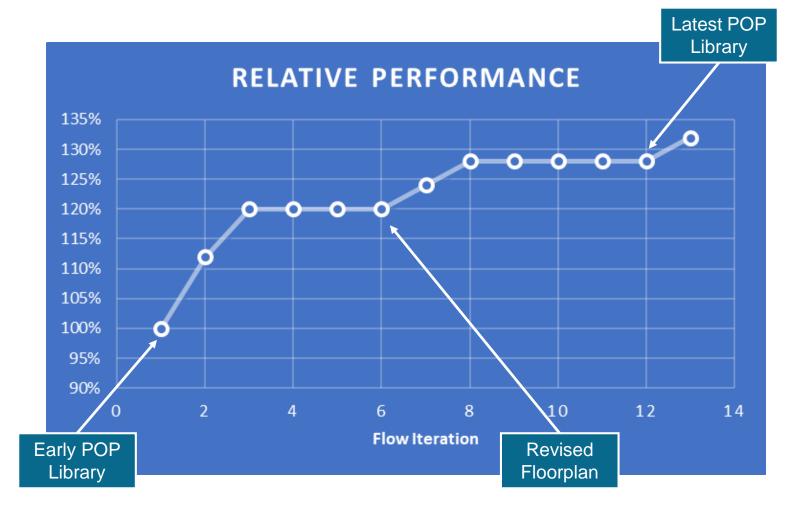
- Complete Cadence RTL-to-GDS digital implementation flow
 - Example flow scripts
 - Example floorplan
 - Application note explaining how to setup the RAK
 - Application notes showing how the flow works
- Customized for latest advanced Arm CPU and Samsung Foundry 5LPE process
- Available to customers enabling fast implementation of latest Arm CPU







Arm Advanced CPU 5LPE High-Performance RAK Results



- Arm, Samsung Foundry, and Cadence working together have enabled over 30% performance improvements
- More to come as collaboration continues
- Customers have immediate access to improved results using RAK

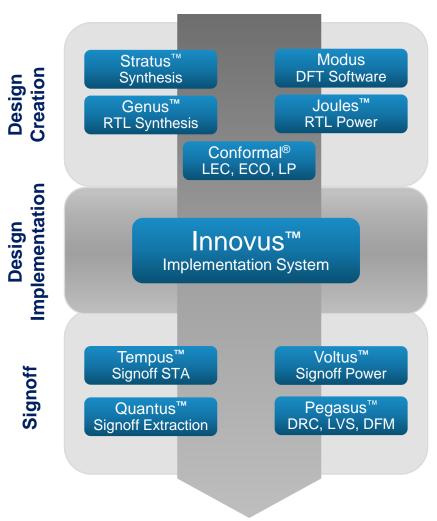
Over 30% performance improvement achieved so far .. More to come







Delivering Design Excellence for 5LPE Arm CPU Implementation



- Complete Cadence high-performance digital implementation and signoff flow
- Fully qualified for Samsung Foundry 5LPE
 - 5LPE process and tool co-optimization
 - One simple command to enable 5LPE set-up
 - 5LPE Statistical Via Timing Analysis and Optimization
- Tuned and proven on Arm high-performance CPU and POP library for outstanding PPA
- Common user interface and FlowKit included as part of Rapid Adoption Kit







arm

SAMSUNG FOUNDRY

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